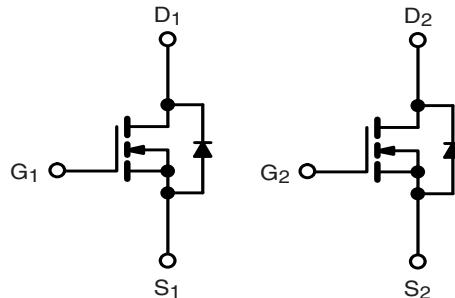


## General Description

The AO4826 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for use as a load switch or in PWM applications.

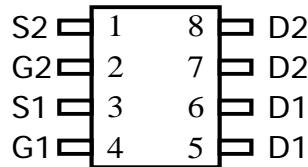


## General Features

$V_{DS} = 60V$   $I_D = 6.3A$

$R_{DS(ON)} < 25m\Omega$  @  $V_{GS}=10V$

$R_{DS(ON)} < 30m\Omega$  @  $V_{GS}=4.5V$



## ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ C$ , unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current	$I_D$	7	A
		4	
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	3.6	
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	28	
Single Pulse Avalanche Current	$I_{AS}$	18	mJ
Single Pulse Avalanche Energy	$E_{AS}$	16.2	
Maximum Power Dissipation <sup>b</sup>	$P_D$	4	W
		1.3	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +175	°C

## THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	$R_{thJA}$	110	°C/W
Junction-to-Foot (Drain)	$R_{thJF}$	34	

### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300 \mu s$ , duty cycle  $\leq 2\%$ .
- c. When mounted on 1" square PCB (FR4 material).

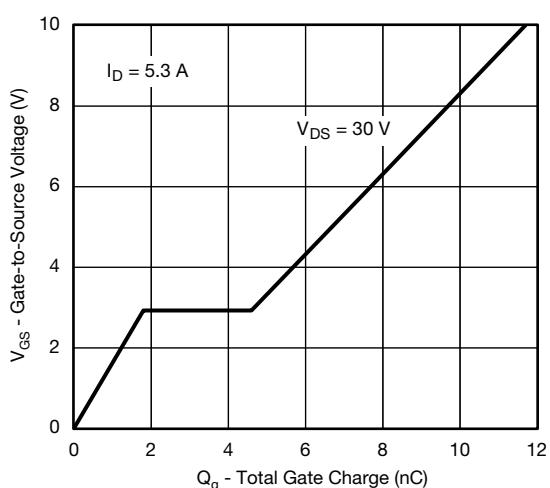
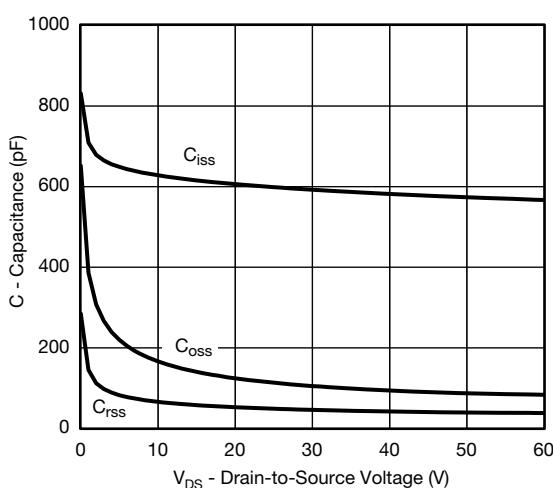
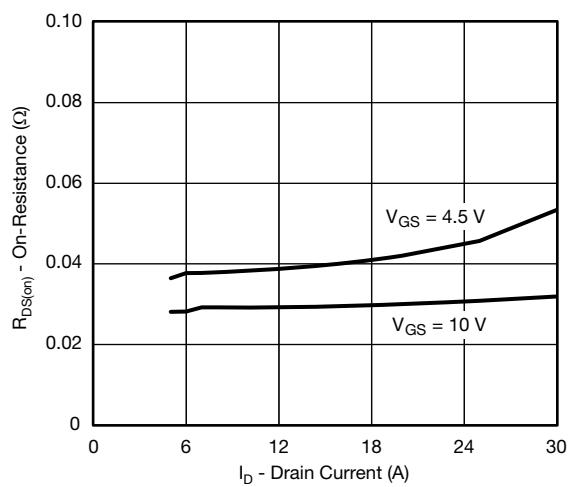
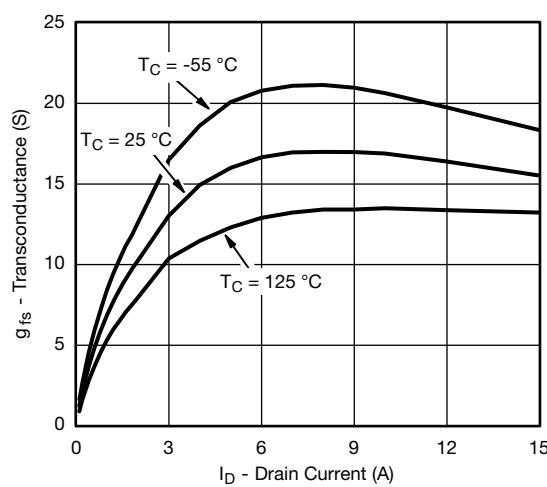
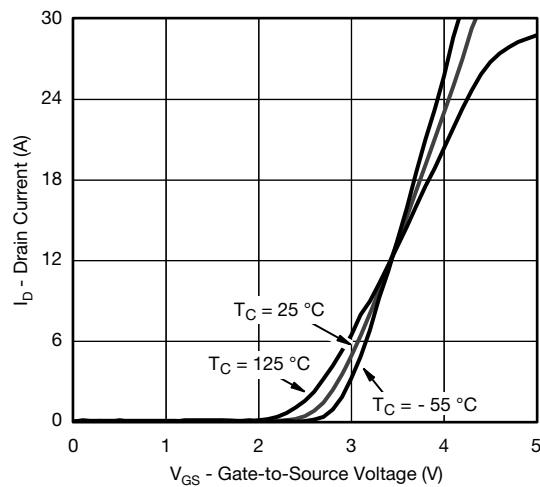
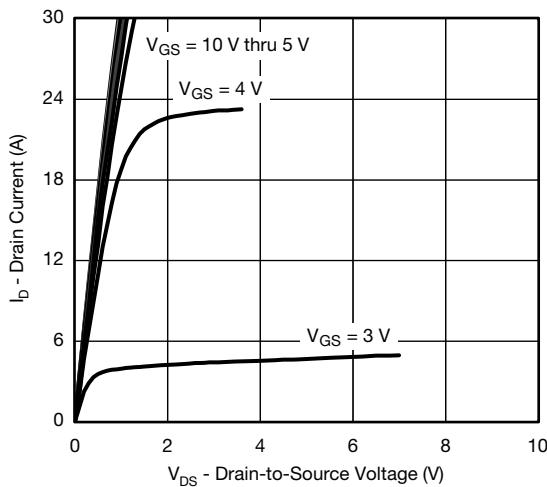
**SPECIFICATIONS** ( $T_C = 25^\circ\text{C}$ , unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$		60	-	-	V	
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$ , $I_D = 250 \mu\text{A}$		1	1.5	2.5		
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}$ , $V_{GS} = \pm 20 \text{ V}$		-	-	$\pm 100$	nA	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0 \text{ V}$	$V_{DS} = 60 \text{ V}$	-	-	1	$\mu\text{A}$	
		$V_{GS} = 0 \text{ V}$	$V_{DS} = 60 \text{ V}$ , $T_J = 125^\circ\text{C}$	-	-	50		
		$V_{GS} = 0 \text{ V}$	$V_{DS} = 60 \text{ V}$ , $T_J = 175^\circ\text{C}$	-	-	150		
On-State Drain Current <sup>a</sup>	$I_{D(\text{on})}$	$V_{GS} = 10 \text{ V}$	$V_{DS} \geq 5 \text{ V}$	20	-	-	A	
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$	$I_D = 4.5 \text{ A}$		20	25	$\text{m}\Omega$	
		$V_{GS} = 4.5 \text{ V}$	$I_D = 4 \text{ A}$		22	30		
Forward Transconductance <sup>f</sup>	$g_{fs}$	$V_{DS} = 15 \text{ V}$ , $I_D = 4.5 \text{ A}$		-	15	-	S	
Input Capacitance	$C_{iss}$	$V_{GS} = 0 \text{ V}$	$V_{DS} = 25 \text{ V}$ , $f = 1 \text{ MHz}$	-	600	750	$\text{pF}$	
Output Capacitance	$C_{oss}$			-	110	140		
Reverse Transfer Capacitance	$C_{rss}$			-	50	62		
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{GS} = 10 \text{ V}$	$V_{DS} = 30 \text{ V}$ , $I_D = 5.3 \text{ A}$	-	11.7	18	$\text{nC}$	
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			-	1.8	2.7		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			-	2.8	4.2		
Gate Resistance	$R_g$	$f = 1 \text{ MHz}$		1.3	-	6	$\Omega$	
Turn-On Delay Time <sup>c</sup>	$t_{d(\text{on})}$	$V_{DD} = 30 \text{ V}$ , $R_L = 6.8 \Omega$ $I_D \equiv 4.4 \text{ A}$ , $V_{GEN} = 10 \text{ V}$ , $R_g = 1 \Omega$		-	7	11	$\text{ns}$	
Rise Time <sup>c</sup>	$t_r$			-	3.3	5		
Turn-Off Delay Time <sup>c</sup>	$t_{d(\text{off})}$			-	22.4	33.5		
Fall Time <sup>c</sup>	$t_f$			-	2.1	3.2		
Pulsed Current <sup>a</sup>	$I_{SM}^b$			-	-	28	A	
Forward Voltage	$V_{SD}$	$I_F = 2 \text{ A}$ , $V_{GS} = 0 \text{ V}$		-	0.75	1.1	V	

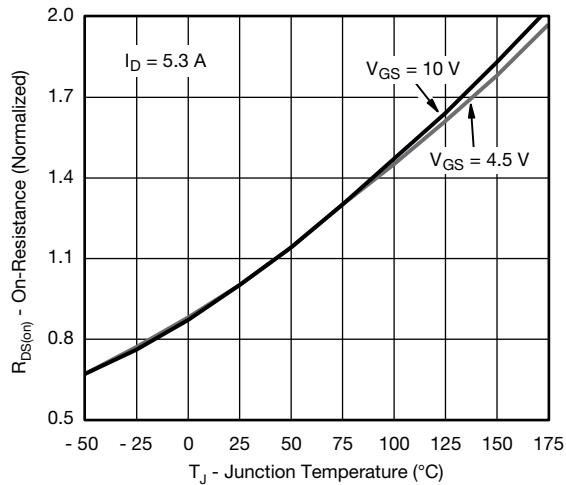
**Notes**

- a. Pulse test; pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2 \%$ .
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

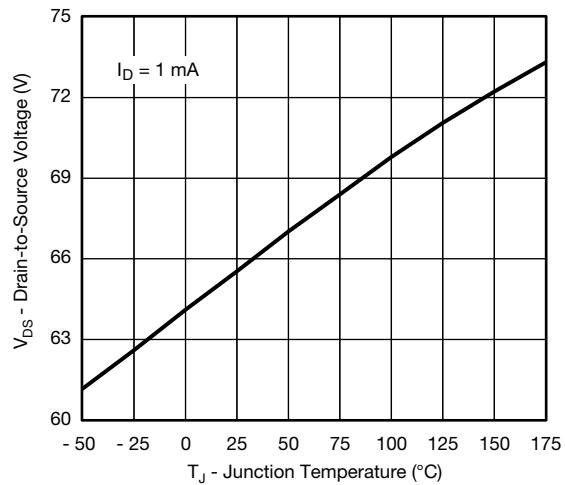
**TYPICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)



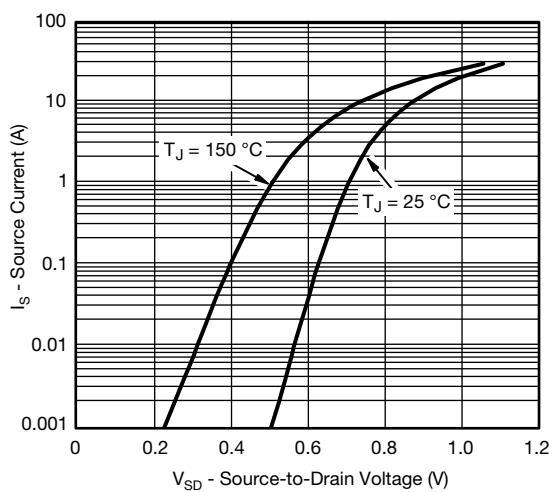
**TYPICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)



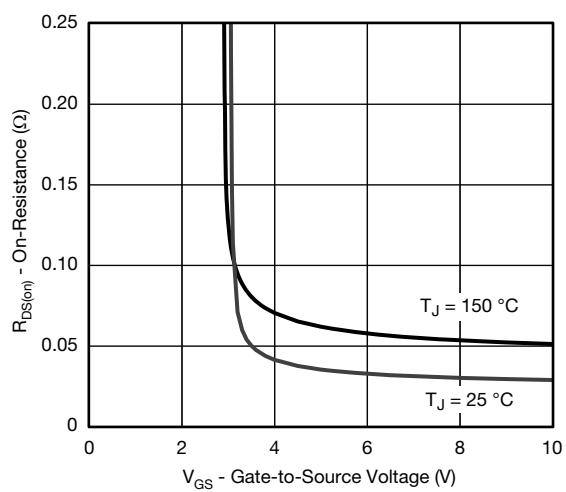
On-Resistance vs. Junction Temperature



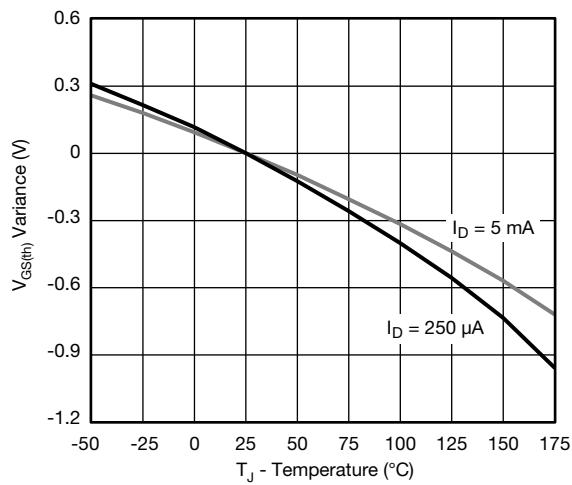
Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage

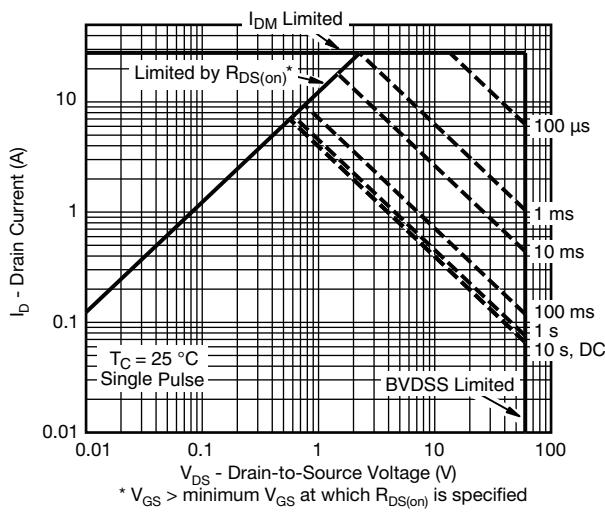


On-Resistance vs. Gate-to-Source Voltage

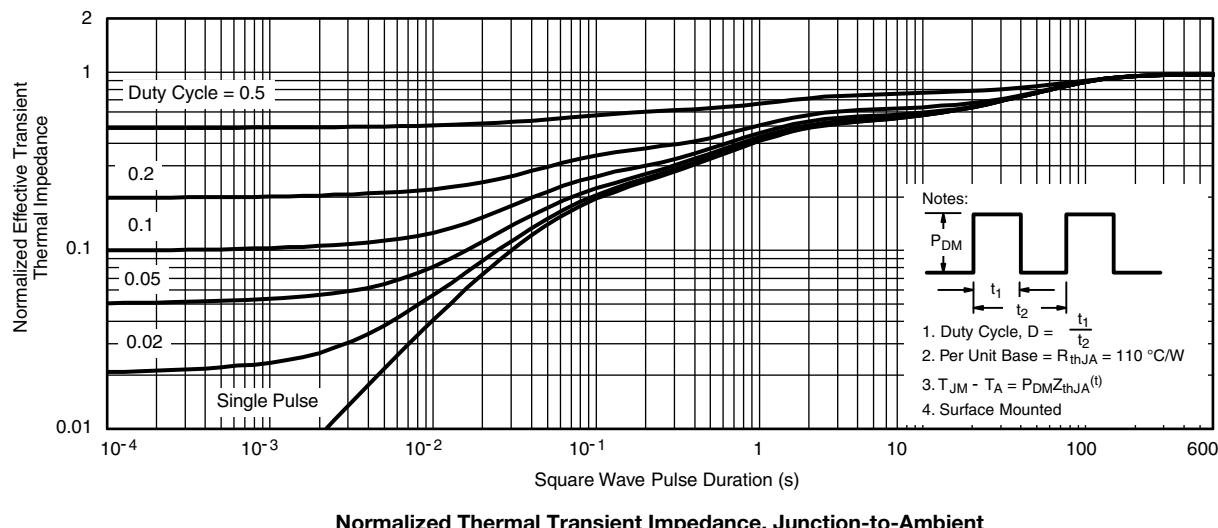


Threshold Voltage

**THERMAL RATINGS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

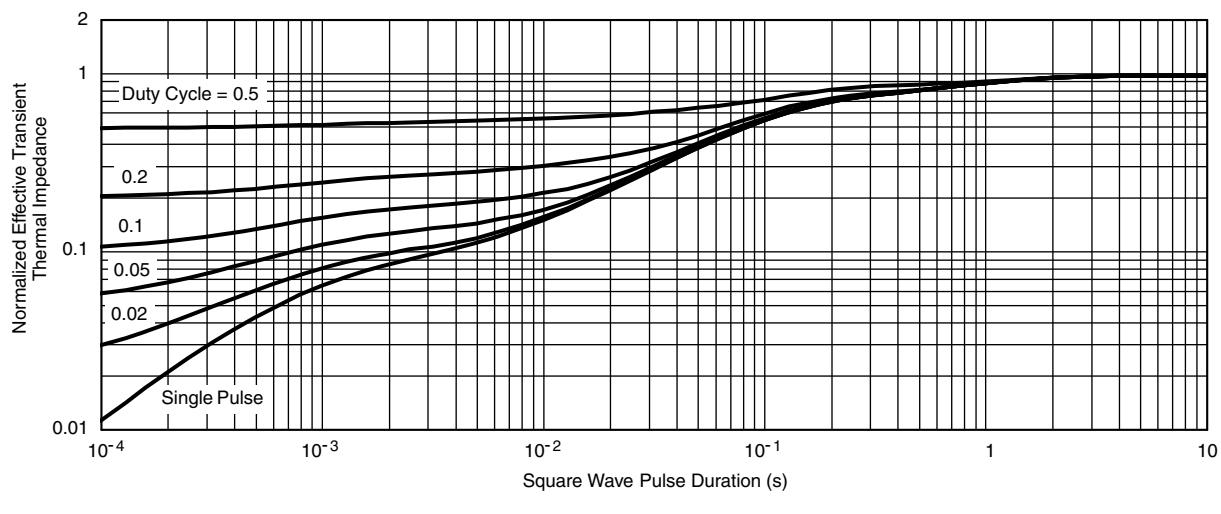


**Safe Operating Area**



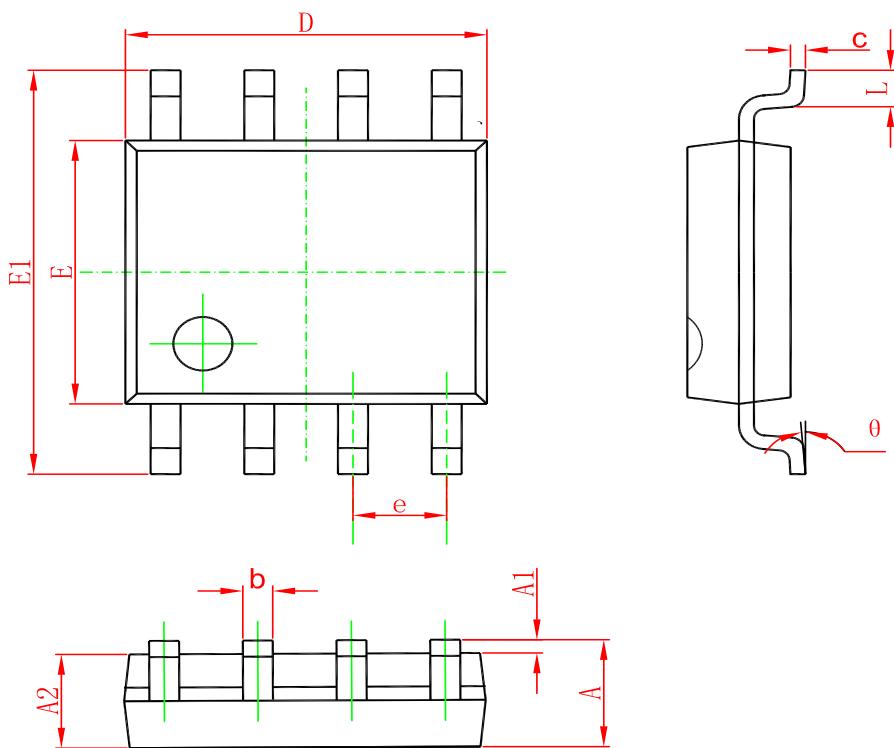
**Normalized Thermal Transient Impedance, Junction-to-Ambient**

**THERMAL RATINGS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)



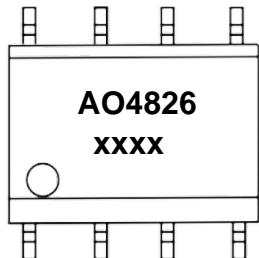
Dual N-Channel MOSFET

SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

## Marking



("xxxx"代表年份周期)

## Ordering information

Order code	Package	Baseqty	Deliverymode
AO4826	SOP-8	3000	Tape and reel